

M2M-1000-170D

Silicon Carbide Power MOSFET

N-Channel Enhancement Mode

- Pulsed Power applications

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

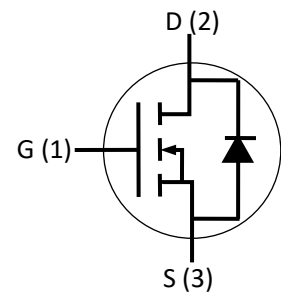
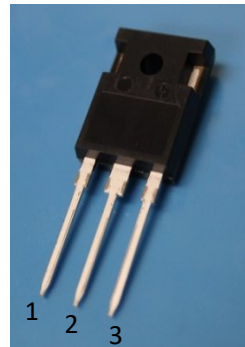
Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives

Package



Part Number	Package
M2M-1000-170D	TO-247-3

Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	1700	V	$V_{GS}=0V, I_D=100\mu A$	
V_{GSmax}	Gate - Source Voltage	-10/+25	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	-5/+20	V	Recommended operational values	
I_D	Continuous Drain Current	5.0 3.6	A	$V_{GS}=20V, T_c=25^\circ\text{C}$ $V_{GS}=20V, T_c=100^\circ\text{C}$	
P_D	Power Dissipation	60	W	$T_c=25^\circ\text{C}, T_J=150^\circ\text{C}$	Fig. 10
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$		

Electrical Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	1700			V	$V_{GS}=0V, I_D=100\mu A$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	2.6	4.0	V	$V_{GS}=V_{DS}, I_{DS}=5mA, T_C=25^\circ C$	Fig. 6
			1.73			$V_{GS}=V_{DS}, I_{DS}=5mA, T_C=150^\circ C$	
I_{DSS}	Zero Gate Voltage Drain Current		1	100	μA	$V_{DS}=1200V, V_{GS}=0V$	
I_{GSS}	Gate-Source Leakage Current		20	200	nA	$V_{GS}=20V, V_{DS}=0V$	
$R_{DS(on)}$	Drain-Source on-state Resistance		650	750	m Ω	$V_{GS}=20V, I_D=2A, T_C=25^\circ C$	Fig. 4
			955			$V_{GS}=20V, I_D=2A, T_C=150^\circ C$	
g_{fs}	Transconductance		1.2		S	$V_{GS}=20V, I_D=2A, T_J=25^\circ C$	Fig. 5
			1.0			$V_{GS}=20V, I_D=2A, T_J=150^\circ C$	
C_{iss}	Input Capacitance		380		pF	$V_{GS}=0V, V_{DS}=1000V, f=1MHz$ $V_{AC}=25mV$	Fig. 8
C_{oss}	Output Capacitance		15				
C_{rss}	Reverse Transfer Capacitance		3.3				
E_{ON}	Turn-On Switching Energy		36		μJ	$V_{DS}=120V, V_{GS}=-5/20V, I_D=2A,$ $R_{G(ext)}=2.5\Omega, L=1478\mu H$	
E_{OFF}	Turn-Off Switching Energy		15				
$t_{d(on)}$	Turn-On Delay Time		6		ns	$V_{DD}=1200V, V_{GS}=-5/20V$ $I_D=2A, R_{G(ext)}=2.5\Omega,$ $R_L=600\Omega, \text{Timing relative to } V_{DS}$	
t_r	Rise Time		9.5				
$t_{d(off)}$	Turn-Off Delay Time		14.3				
t_f	Fall Time		22				
$R_{G(int)}$	Internal Gate Resistance		20		Ω	$f=1MHz, V_{AC}=25mV$	
Q_{gs}	Gate to Source Charge		4.8		nC	$V_{DD}=800V, V_{GS}=-5/20V$ $I_D=20A$	Fig. 9
Q_{gd}	Gate to Drain Charge		5.6				
Q_g	Total Gate Charge		13				

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.5		V	$V_{GS}=-5V, I_{SD}=1A, T_J=25^\circ C$	Fig. 7
		3.3		V	$V_{GS}=-5V, I_{SD}=1A, T_J=150^\circ C$	
I_S	Continuous Diode Forward Current		4	A	$T_C=25^\circ C$	

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t_{rr}	Reverse Recovery time	22	ns	$V_{GS} = -5V, I_{SD} = 2 A, V_R = 1200V,$ $dif/dt=1200A/\mu s;$
Q_{rr}	Reverse Recovery Charge	31	nC	
I_{rrm}	Peak Reverse Recovery Current	3.5	A	

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.8	$^{\circ}C/W$		Fig. 11
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	40			

Typical Performance

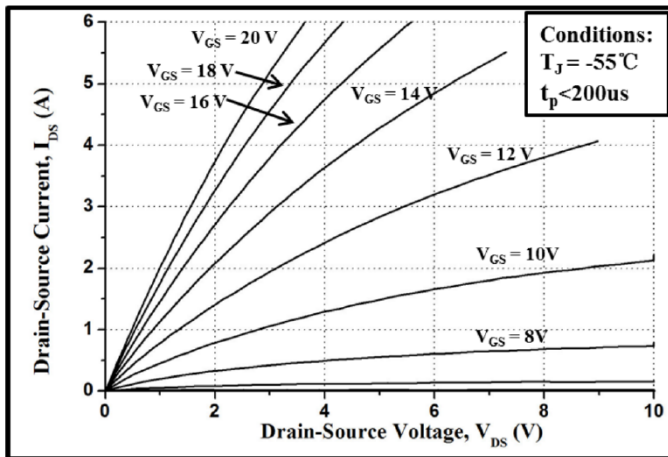


Figure 1. Output Characteristics $T_J = -55^{\circ}C$

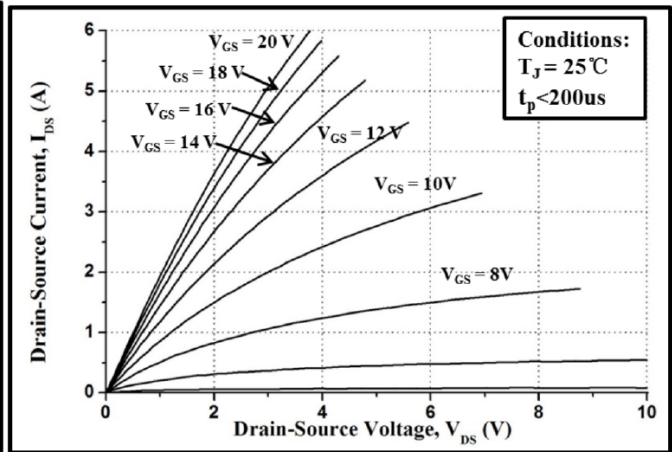


Figure 2. Output Characteristics $T_J = 25^{\circ}C$

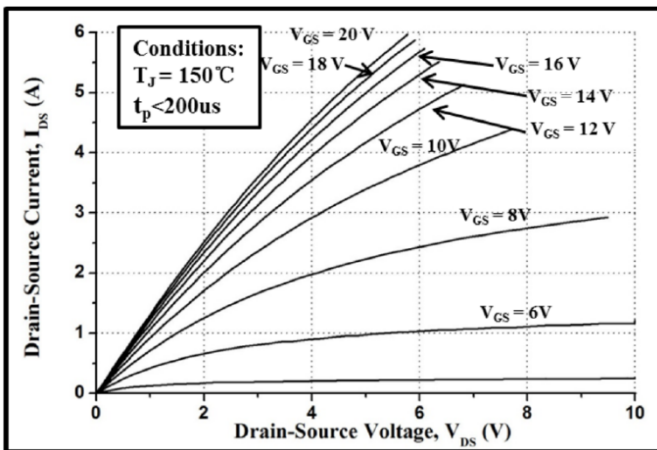


Figure 3. Output Characteristics $T_J = 150^{\circ}C$

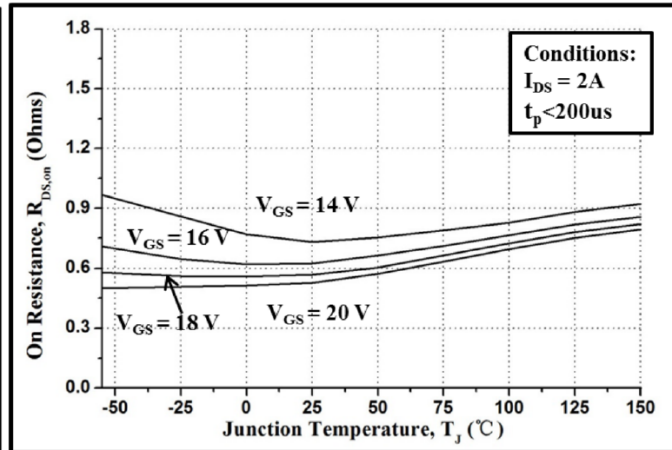


Figure 4. On-Resistance For Various Gate Voltage

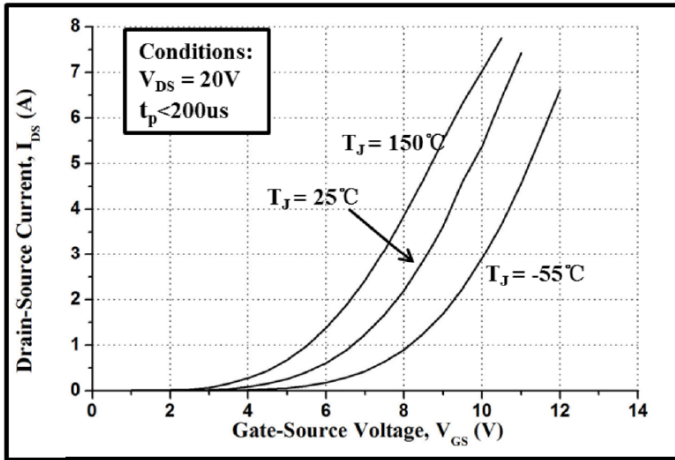


Figure 5. Transfer Characteristic for Various Junction Temperatures

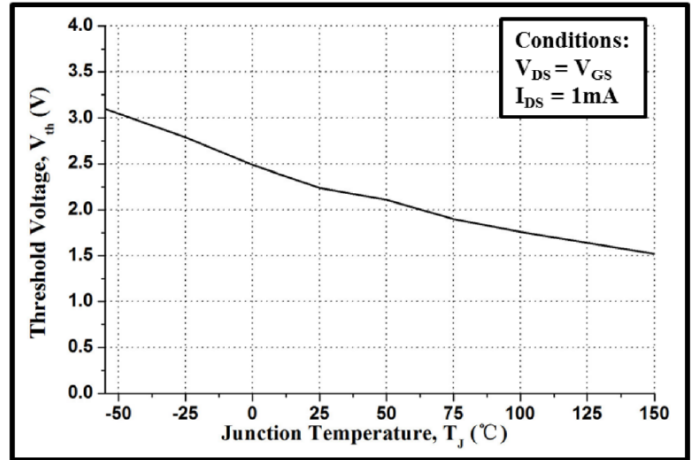


Figure 6. Threshold Voltage vs. Temperature

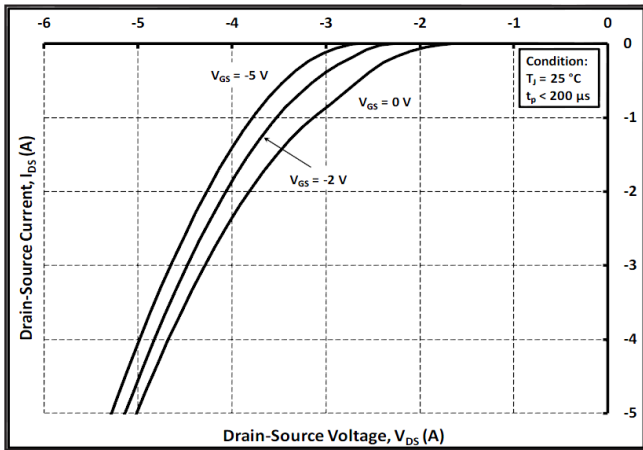


Figure 7. Body Diode Characteristics

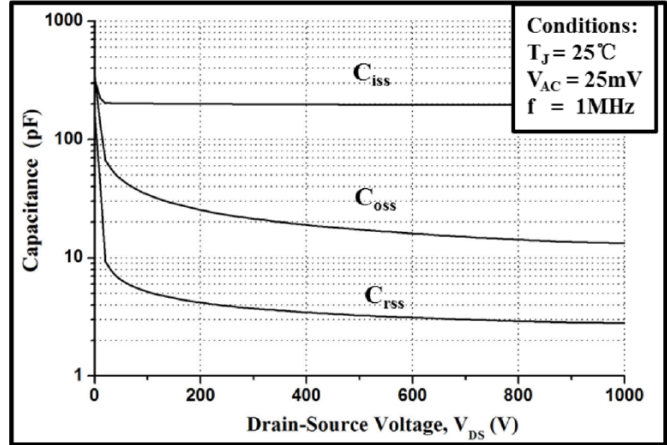


Figure 8. Capacitances vs. Drain-Source Voltage

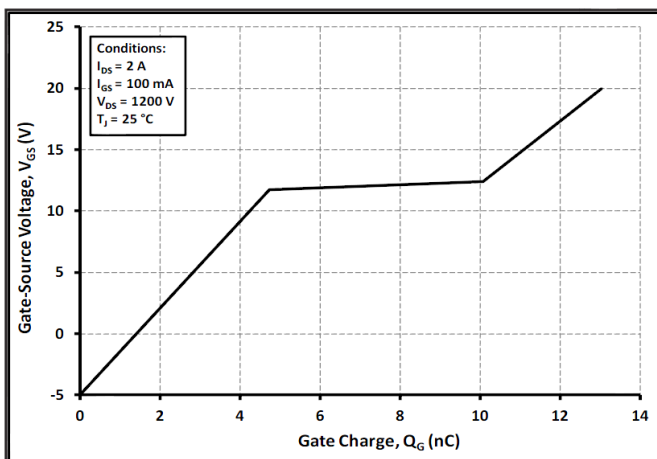


Figure 9. Gate Charge Characteristics

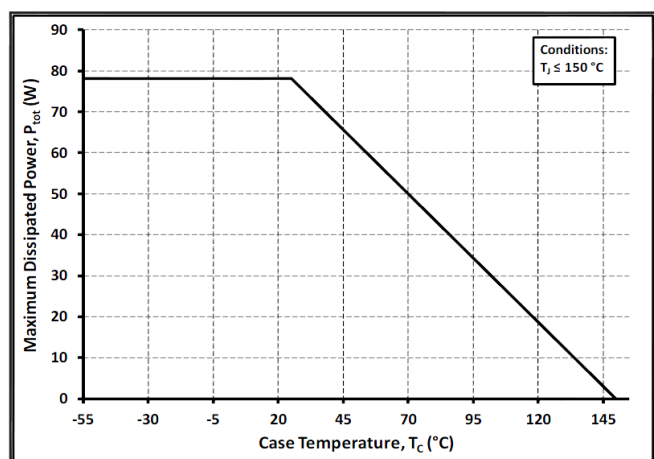


Figure 10. Power Dissipation Derating

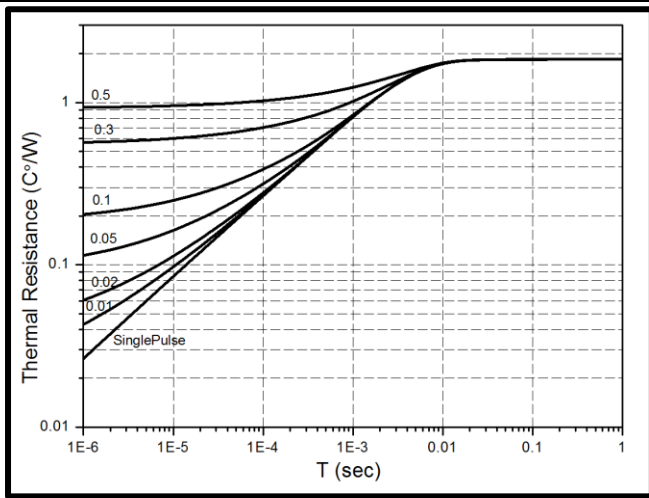


Figure 11. Transient Thermal Impedance

Package Dimensions: TO-247-3L

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